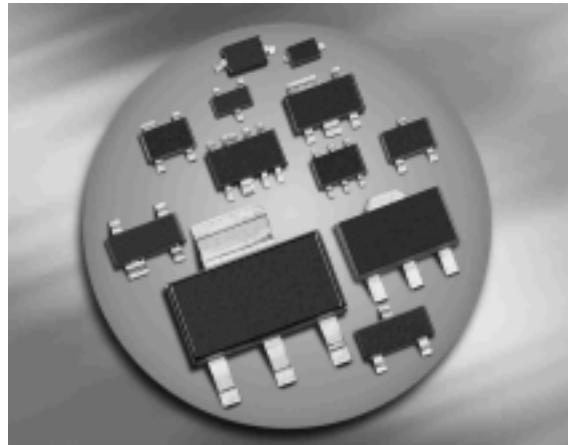
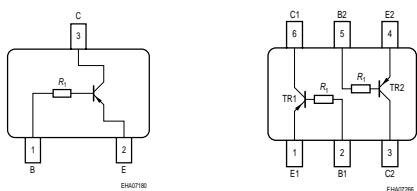


### PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ( $R_1 = 4.7 \text{ k}\Omega$ )
- BCR169S: Two internally isolated transistors with good matching in one multichip package
- BCR169S: For orientation in reel see package information below
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101


**BCR169/F/W**
**BCR169S**


Type	Marking	Pin Configuration						Package
BCR169	WSs	1=B	2=E	3=C	-	-	-	SOT23
BCR169F	WSs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR169S	WSs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BCR169W	WSs	1=B	2=E	3=C	-	-	-	SOT323

<sup>1)</sup>Pb-containing package may be available upon special request

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	50	V
Collector-base voltage	$V_{CBO}$	50	
Input forward voltage	$V_i(fwd)$	30	
Input reverse voltage	$V_i(rev)$	5	
Collector current	$I_C$	100	mA
Total power dissipation BCR169, $T_S \leq 102^\circ\text{C}$ BCR169F, $T_S \leq 128^\circ\text{C}$ BCR169S, $T_S \leq 115^\circ\text{C}$ BCR169W, $T_S \leq 124^\circ\text{C}$	$P_{tot}$	200 250 250 250	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup> BCR169 BCR169F BCR169S BCR169W	$R_{thJS}$	$\leq 240$ $\leq 90$ $\leq 140$ $\leq 105$	K/W

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

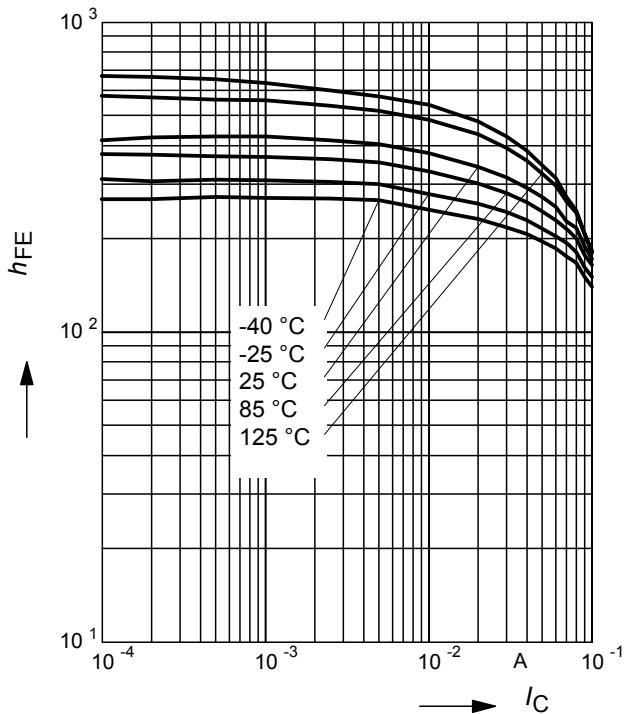
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(\text{BR})\text{CEO}}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(\text{BR})\text{CBO}}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	$I_{\text{CBO}}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 5 \text{ V}, I_C = 0$	$I_{\text{EBO}}$	-	-	100	nA
DC current gain <sup>1)</sup> $I_C = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	$h_{\text{FE}}$	120	-	630	-
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	$V_{\text{CEsat}}$	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(\text{off})}$	0.4	-	0.8	
Input on voltage $I_C = 2 \text{ mA}, V_{CE} = 0.3 \text{ V}$	$V_{i(\text{on})}$	0.5	-	1.1	
Input resistor	$R_1$	3.2	4.7	6.2	k $\Omega$

**AC Characteristics**

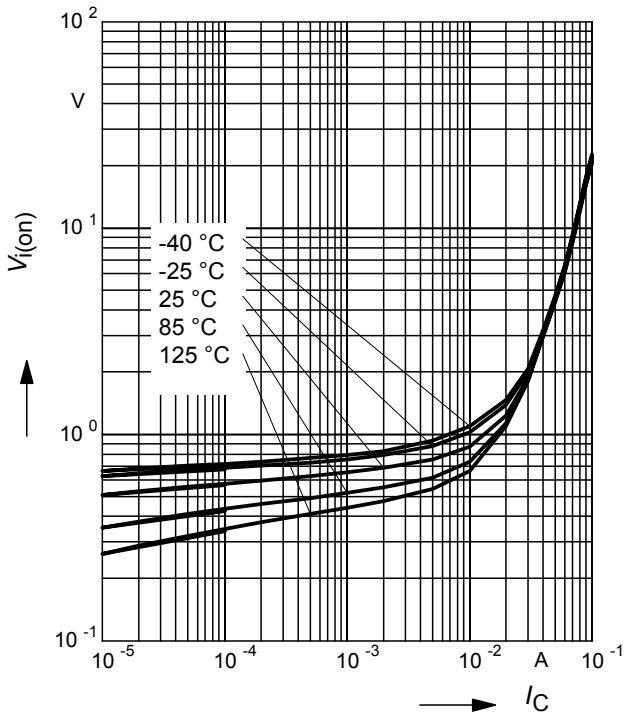
Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	$f_T$	-	200	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	$C_{cb}$	-	3	-	pF

<sup>1</sup>Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

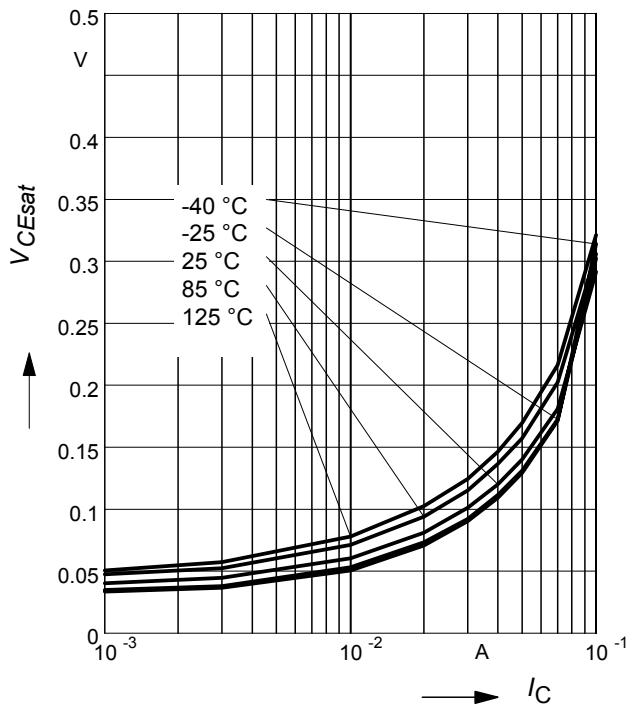
**DC current gain**  $h_{FE} = f(I_C)$   
 $V_{CE} = 5 \text{ V}$  (common emitter configuration)



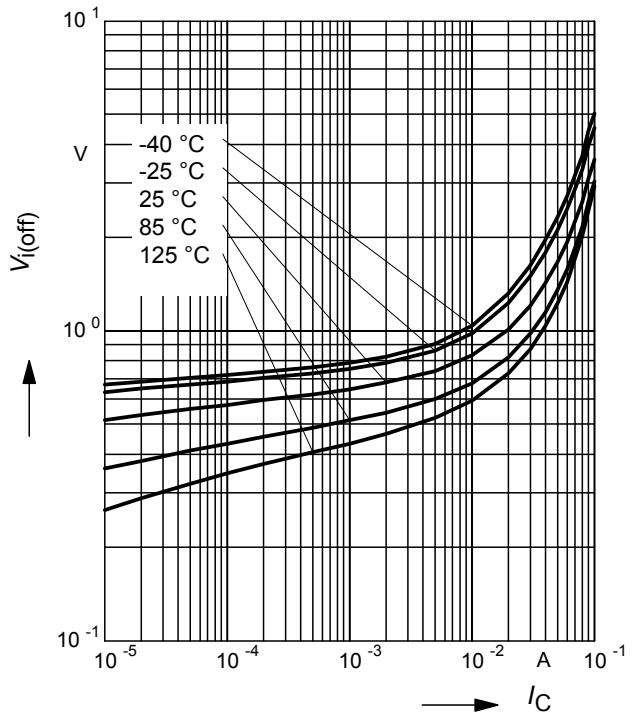
**Input on Voltage**  $V_{i(on)} = f(I_C)$   
 $V_{CE} = 0.3 \text{ V}$  (common emitter configuration)



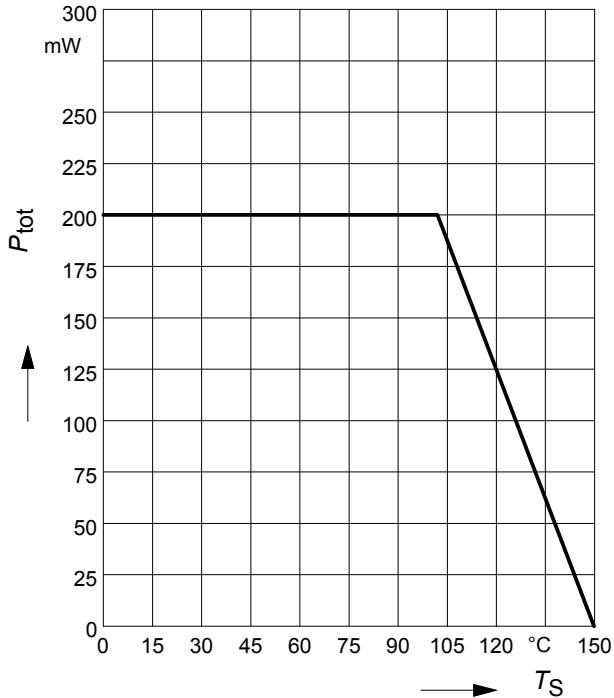
**Collector-emitter saturation voltage**  
 $V_{CEsat} = f(I_C)$ ,  $h_{FE} = 20$



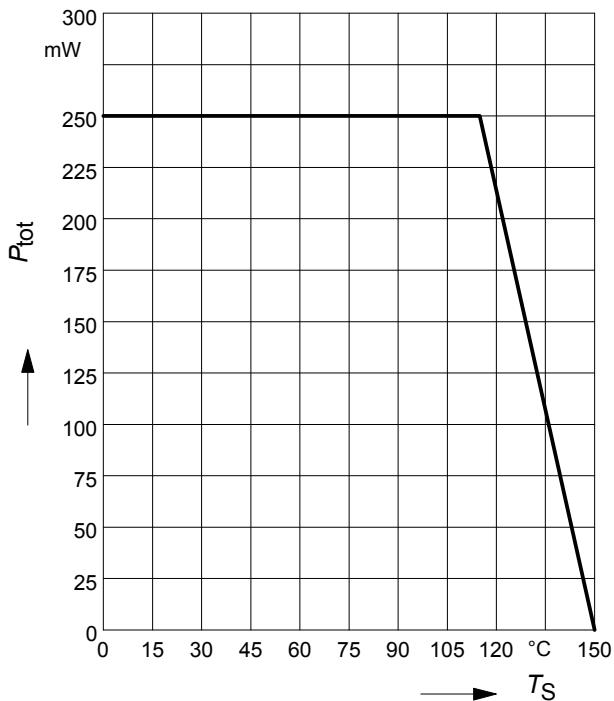
**Input off voltage**  $V_{i(off)} = f(I_C)$   
 $V_{CE} = 5 \text{ V}$  (common emitter configuration)



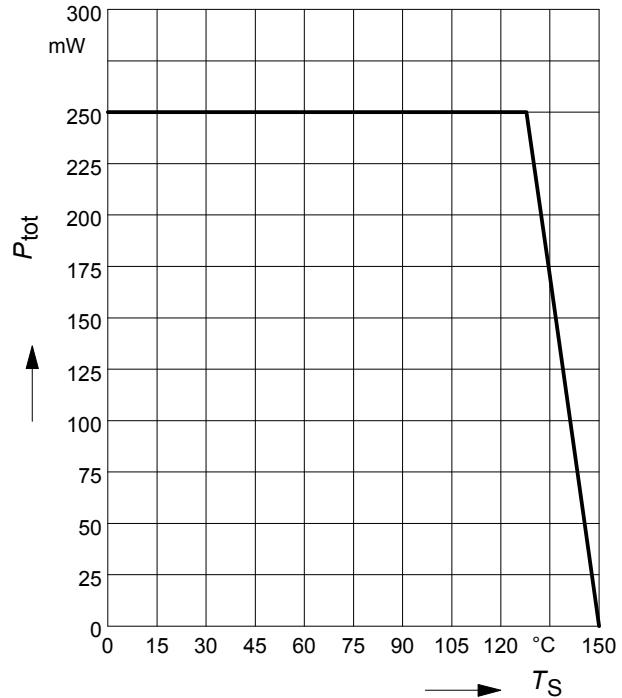
**Total power dissipation  $P_{\text{tot}} = f(T_S)$**   
BCR169



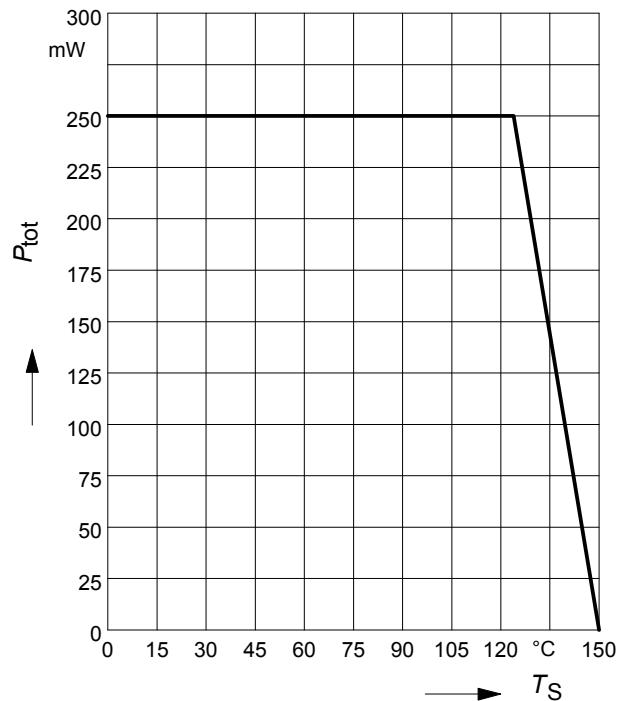
**Total power dissipation  $P_{\text{tot}} = f(T_S)$**   
BCR169S



**Total power dissipation  $P_{\text{tot}} = f(T_S)$**   
BCR169F

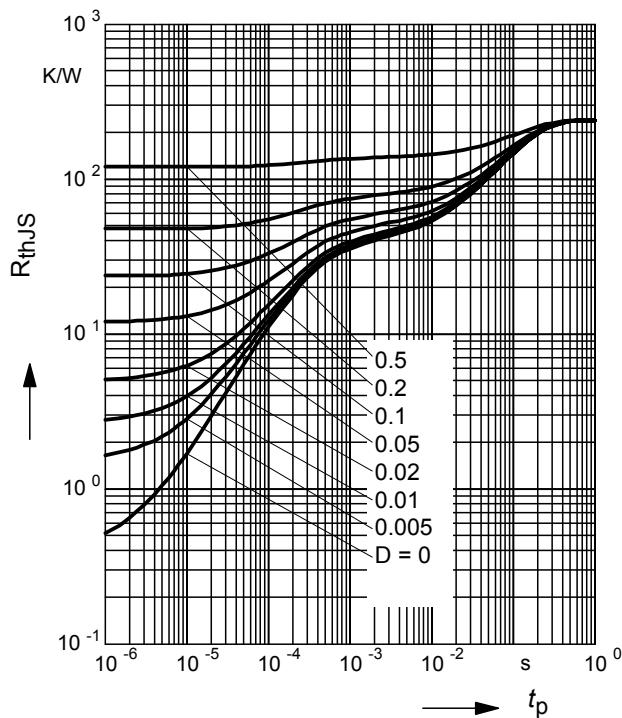


**Total power dissipation  $P_{\text{tot}} = f(T_S)$**   
BCR169W



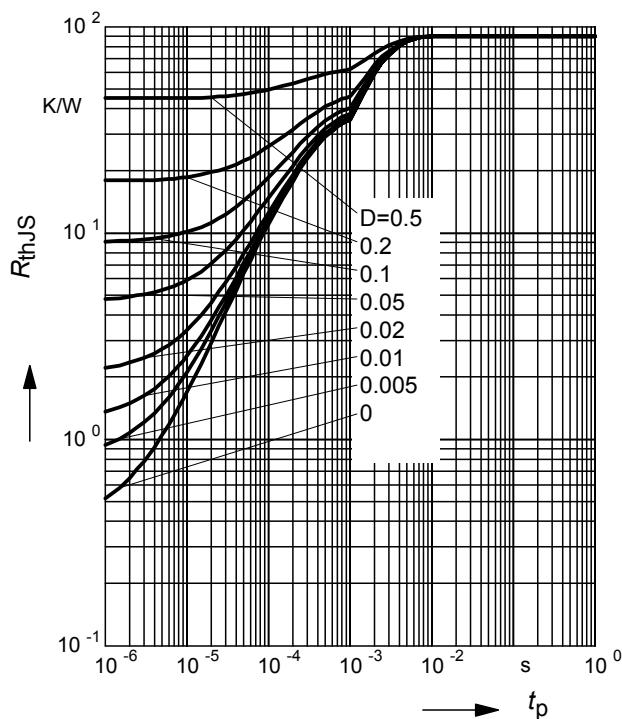
**Permissible Pulse Load  $R_{\text{thJS}} = f(t_p)$**

BCR169



**Permissible Pulse Load  $R_{\text{thJS}} = f(t_p)$**

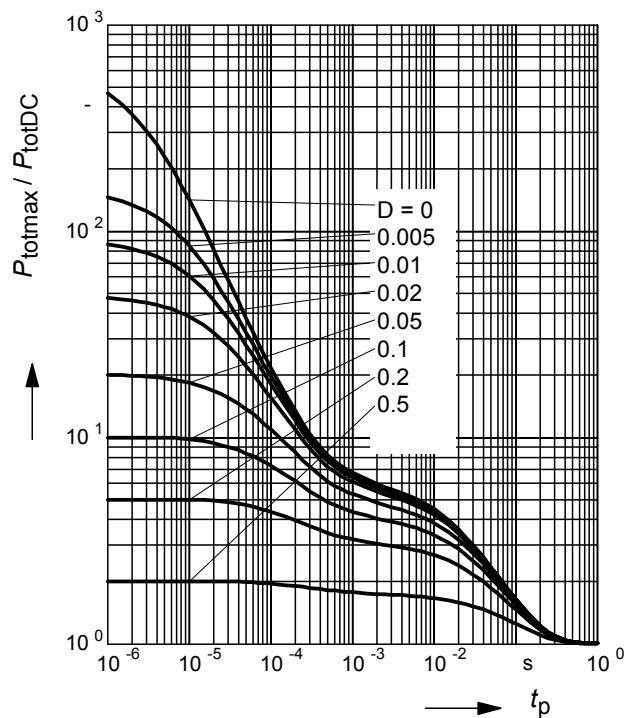
BCR169F



**Permissible Pulse Load**

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$

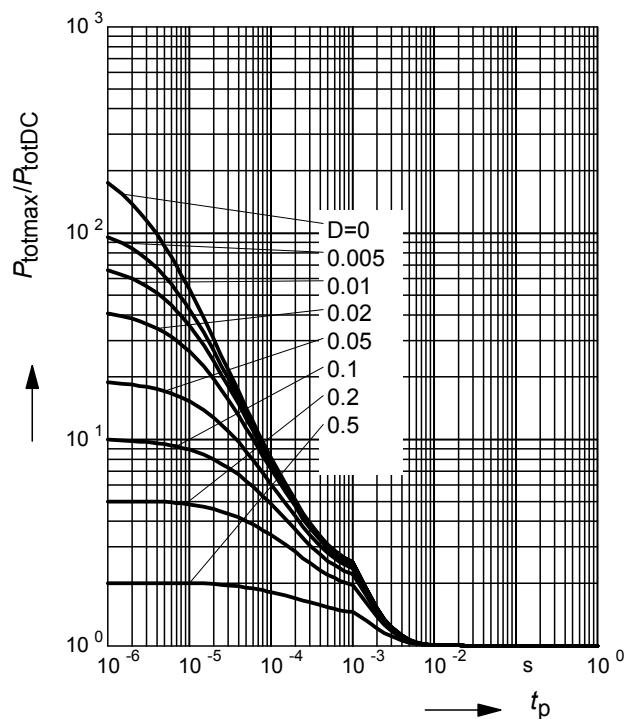
BCR169



**Permissible Pulse Load**

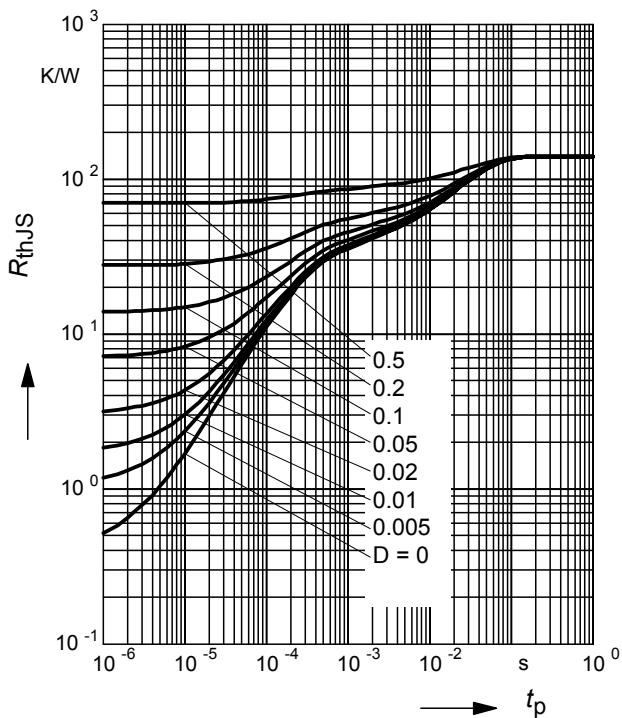
$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$

BCR169F

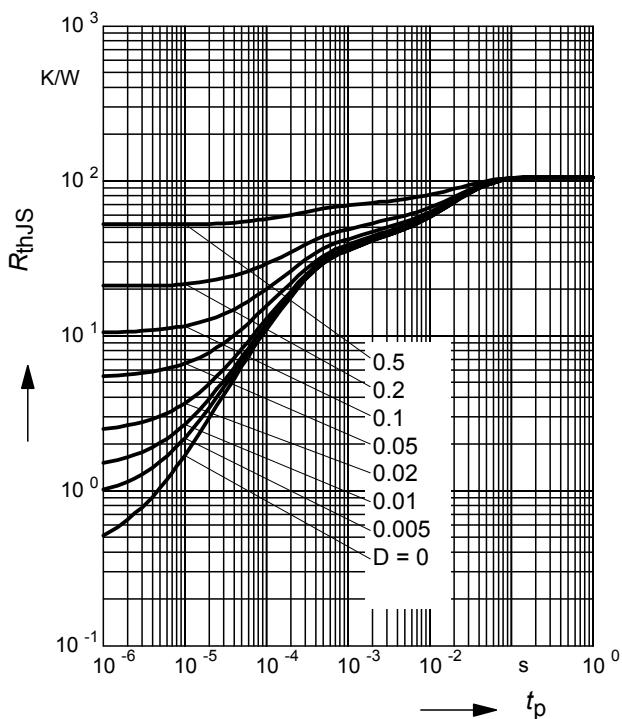


**Permissible Puls Load  $R_{\text{thJS}} = f(t_p)$** 

BCR169S

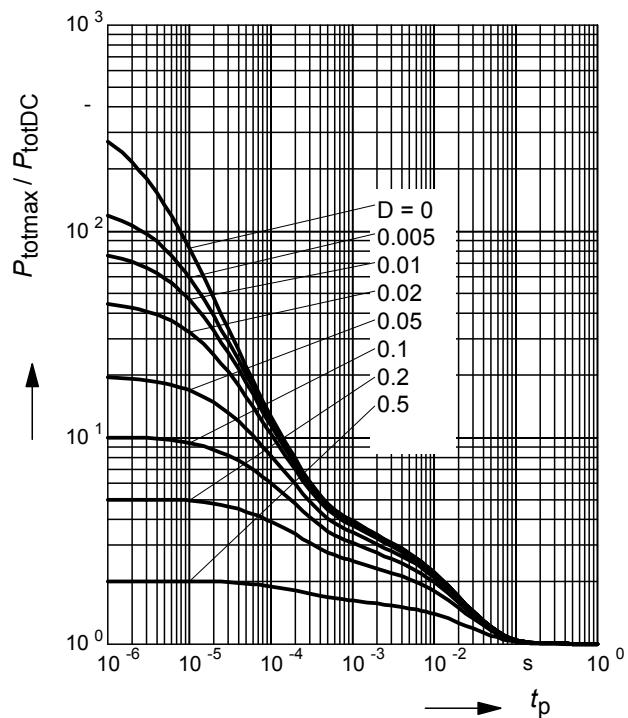

**Permissible Puls Load  $R_{\text{thJS}} = f(t_p)$** 

BCR169W


**Permissible Pulse Load**

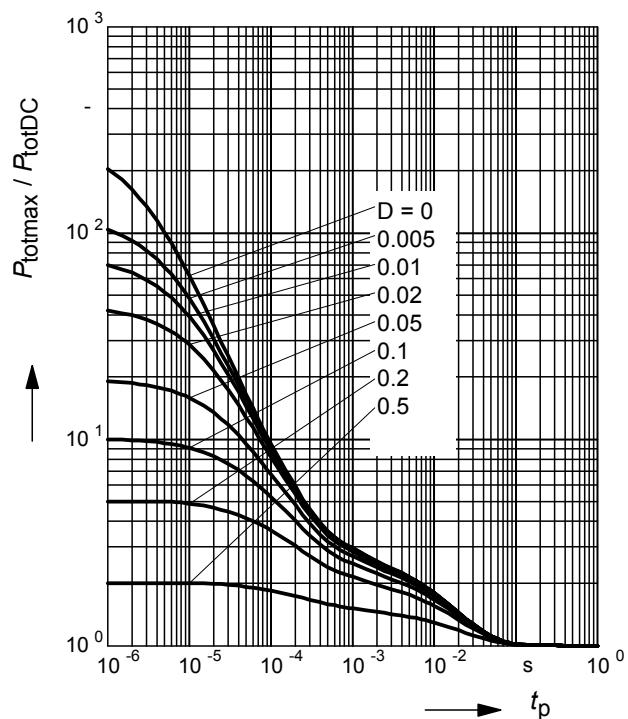
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR169S

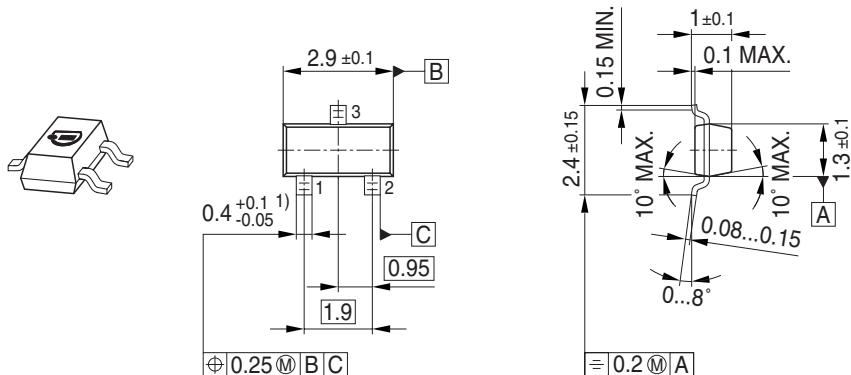

**Permissible Pulse Load**

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR169W

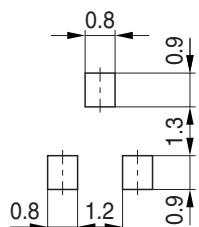


## Package Outline

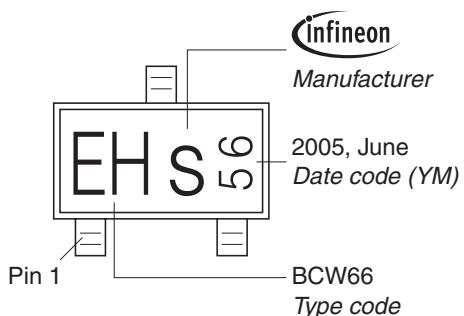


1) Lead width can be 0.6 max. in dambar area

## Foot Print

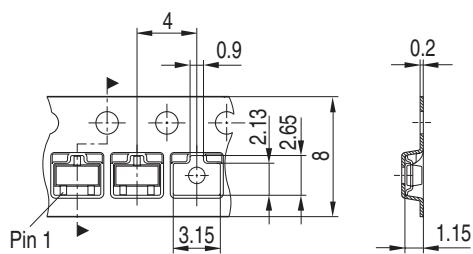


## Marking Layout (Example)

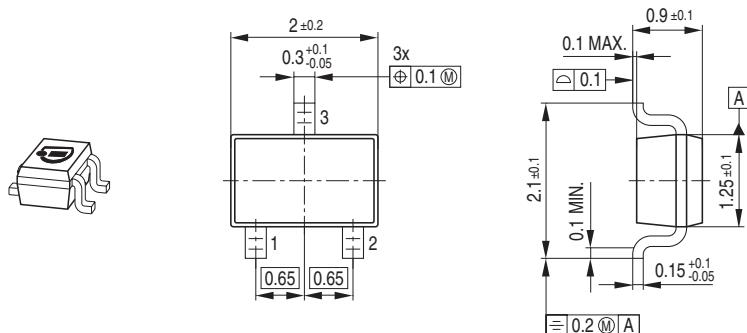


## Standard Packing

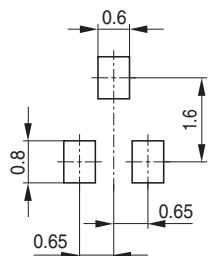
Reel ø180 mm = 3.000 Pieces/Reel  
Reel ø330 mm = 10.000 Pieces/Reel



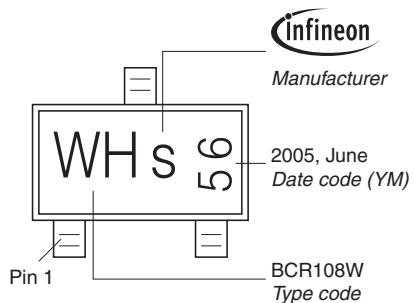
### Package Outline



### Foot Print

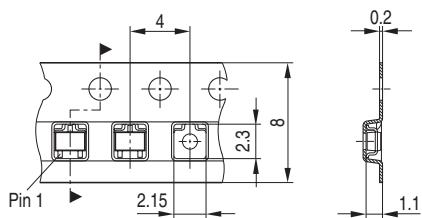


### Marking Layout (Example)

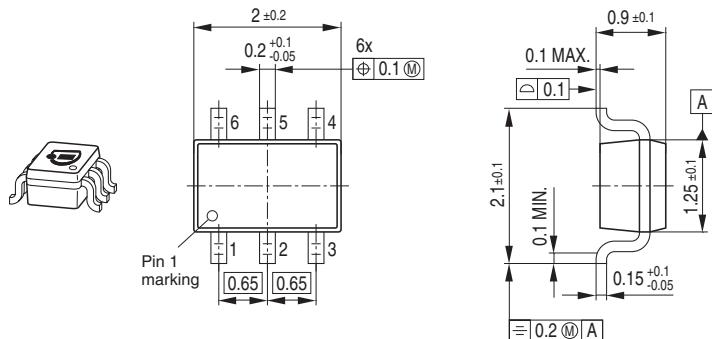


### Standard Packing

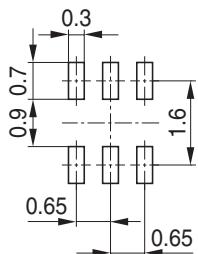
Reel ø180 mm = 3.000 Pieces/Reel  
Reel ø330 mm = 10.000 Pieces/Reel



### Package Outline

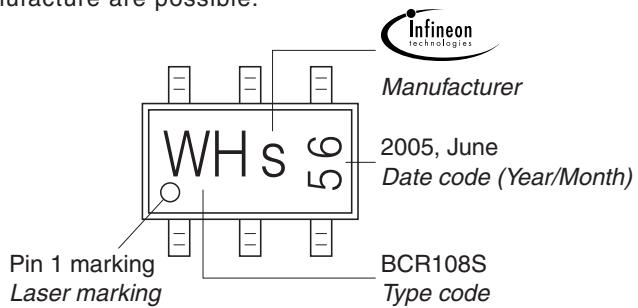


### Foot Print



### Marking Layout (Example)

Small variations in positioning of Date code, Type code and Manufacture are possible.

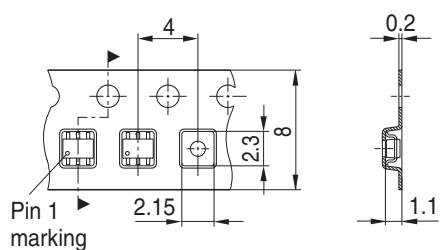


### Standard Packing

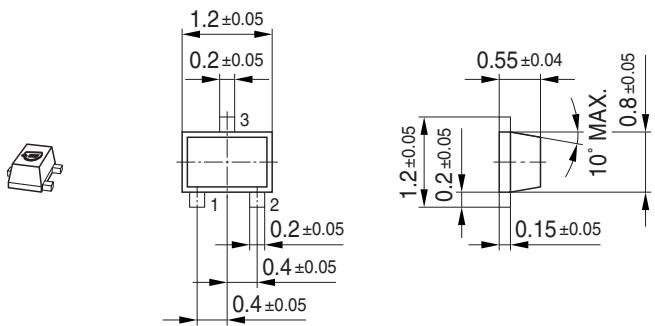
Reel ø180 mm = 3.000 Pieces/Reel

Reel ø330 mm = 10.000 Pieces/Reel

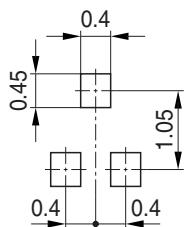
For symmetric types no defined Pin 1 orientation in reel.



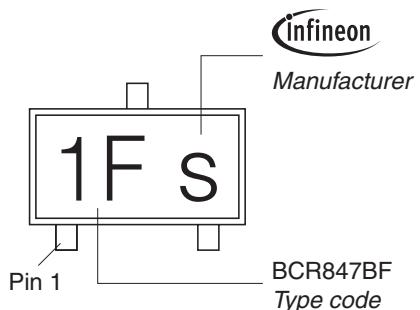
## Package Outline



## Foot Print

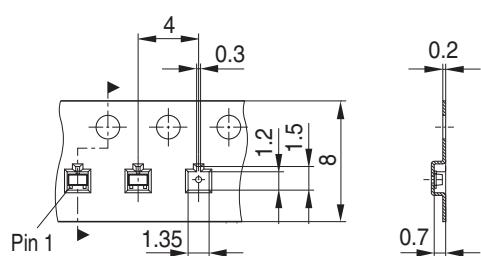


## Marking Layout (Example)



## Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel



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